

MJE270 (NPN), MJE271 (PNP)

Complementary Silicon Power Transistors

- High Safe Operating Area
 $I_{S/B} @ 40 \text{ V}, 1.0 \text{ s} = 0.375 \text{ A}$
- Collector–Emitter Sustaining Voltage
 $V_{CEO(sus)} = 100 \text{ Vdc (Min)}$
- High DC Current Gain
 $h_{FE} @ 120 \text{ mA}, 10 \text{ V} = 1500 \text{ (Min)}$

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	100	Vdc
Collector–Base Voltage	V_{CB}	100	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I_C	2.0 4.0	Adc
Base Current	I_B	0.1	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12	Watts W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 0.012	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	8.33	$^\circ\text{C/W}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	83.3	$^\circ\text{C/W}$

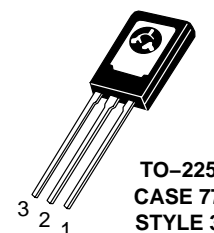
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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**2.0 AMPERE
COMPLEMENTARY
POWER DARLINGTON
TRANSISTORS
100 VOLTS
15 WATTS**



TO-225
CASE 77
STYLE 3

MARKING DIAGRAM



Y = Year
 WW = Work Week
 JE27x = Device Code
 x = 0, 1

ORDERING INFORMATION

Device	Package	Shipping
MJE270	TO-225	500 Units/Box
MJE271	TO-225	500 Units/Box

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	100	–	Vdc
Collector Cutoff Current ($V_{CE} = 100\text{ Vdc}$, $I_B = 0$)	I_{CEO}	–	1.0	mAdc
Collector Cutoff Current ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	0.3	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	0.1	mAdc

SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 40\text{ Vdc}$, $t = 1.0\text{ s}$, Non-repetitive)	$I_{S/b}$	375	–	Adc
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ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 20\text{ mAdc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 120\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	500 1500	– –	–
Collector-Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 0.2\text{ mAdc}$) ($I_C = 120\text{ mAdc}$, $I_B = 1.2\text{ mAdc}$)	$V_{CE(sat)}$	– –	2.0 3.0	Vdc
Base-Emitter On Voltage ($I_C = 120\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	$V_{BE(on)}$	–	2.0	Vdc

DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product (Note 2) ($I_C = 0.05\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	6.0	–	MHz
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1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. $f_T = |h_{fe}| \cdot f_{test}$.

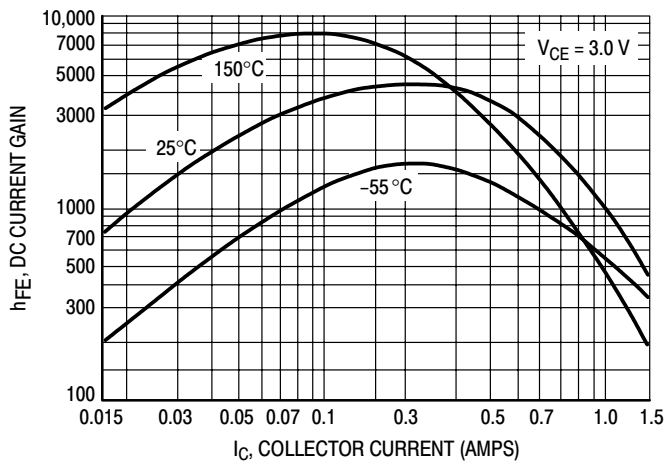


Figure 1. DC Current Gain

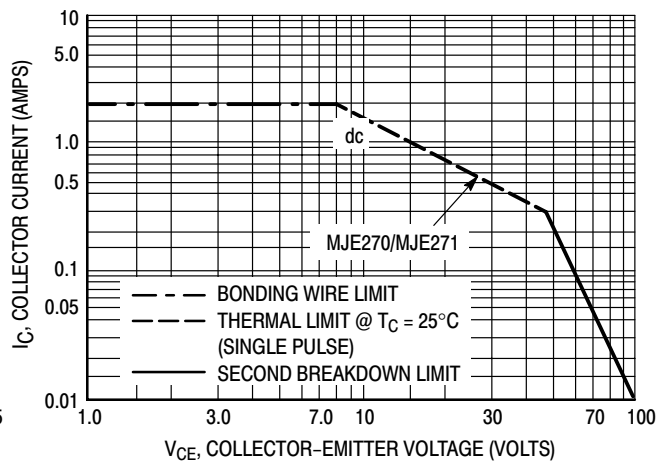
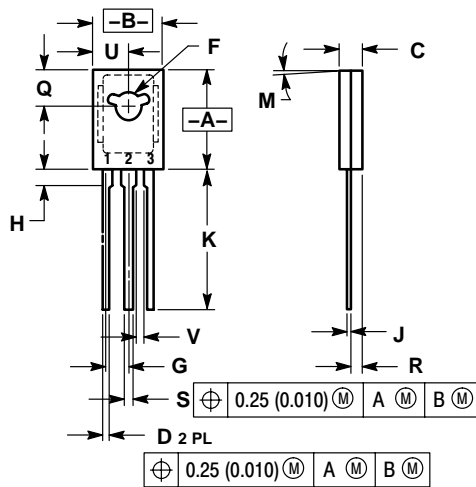


Figure 2. Safe Operating Area

MJE270 (NPN), MJE271 (PNP)

PACKAGE DIMENSIONS

TO-225
CASE 77-09
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 3:

1. BASE
2. COLLECTOR
3. EMITTER

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